## Technical Data

Data Sheet D0206, REV.-

## SD3-0650-S050AB SiC Schottky Power Rectifier Chip



## Description

- 650-Volt Schottky Rectifier
- Zero Reverse Recovery
- Zero Forward Recovery
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on VF

| Part Number | Die Size | Anode | Cathode |
| :---: | :--- | :---: | :---: |
| SD3-0650-S050AB | Please contact your sales representative <br> to get the detailed information about die <br> layout and dimensions. | Al | Ag |

## Maximum Ratings:

| Parameter | Symbol | Value | Units |
| :--- | :---: | :---: | :---: |
| Repetitive Peak Reverse Voltage | $V_{R R M}$ | 650 | V |
| Surge Peak Reverse Voltage | $\mathrm{V}_{\text {RSM }}$ | 650 | V |
| DC Peak Blocking Voltage | $\mathrm{V}_{R}$ | 650 | V |
| Maximum DC Current* | $\mathrm{I}_{\mathrm{F}}$ | 50 | A |
| Repetitive Peak Forward Surge Current | $\mathrm{I}_{\text {FRM }}$ | 121 | A |
| Peak One Cycle Non-Repetitive Surge Current | $\mathrm{I}_{\text {FSM }}$ | 300 | A |
| Operating Junction and Storage Temperature | $\mathrm{T}_{J}, \mathrm{~T}_{\text {stg }}$ | -55 to +175 | ${ }^{\circ} \mathrm{C}$ |

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## Electrical Characteristics(T=25 ${ }^{\circ} \mathrm{C}$ unless otherwise specified):

| Characteristics | Symbol | Condition | Typ. | Max. | Units |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Forward Voltage Drop* | $\mathrm{V}_{\mathrm{F} 1}$ | @ 50A, Pulse, $\mathrm{T}_{J}=25^{\circ} \mathrm{C}$ | 1.5 | 1.7 | V |
|  | $V_{\text {F2 }}$ | @ 50A, Pulse, $\mathrm{T}_{\mathrm{J}}=175{ }^{\circ} \mathrm{C}$ | 2.0 | 2.4 | V |
| Reverse Current* | $\mathrm{I}_{\mathrm{R} 1}$ | $@ \mathrm{~V}_{\mathrm{R}}=$ rated $\mathrm{V}_{\mathrm{R}}, \mathrm{T}_{J}=25^{\circ} \mathrm{C}$ | 1 | 40 | uA |
|  | $\mathrm{I}_{\mathrm{R} 2}$ | $@ \mathrm{~V}_{\mathrm{R}}=$ rated $\mathrm{V}_{\mathrm{R}}, \mathrm{T}_{J}=175{ }^{\circ} \mathrm{C}$ | 10 | 60 | uA |
| Junction Capacitance | $\mathrm{C}_{\top}$ | $\mathrm{V}_{\mathrm{R}}=0 \mathrm{~V}, \mathrm{~T}_{\mathrm{J}}=25^{\circ} \mathrm{C}, \mathrm{f}=1 \mathrm{MHz}$ | 3100 | - | pF |
| Reverse Recovery Charge | Qc | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=50 \mathrm{~A}, \mathrm{di} / \mathrm{dt}=200 \mathrm{~A} / \mu \mathrm{s} \\ & \mathrm{~V}_{\mathrm{R}}=400 \mathrm{~V}, \mathrm{~T}_{J}=25^{\circ} \mathrm{C} \end{aligned}$ | 193.4 | - | nC |
| Capacitance Stored Energy | Ec | $\mathrm{V}_{\mathrm{R}}=400 \mathrm{~V}, \mathrm{~T}_{J}=25^{\circ} \mathrm{C}$ | 47.37 | - | $\mu \mathrm{J}$ |

* Pulse width < 300 ss, duty cycle < 2\%


## Mechanical Parameters:

| Parameter | Typ. | Unit |
| :--- | :---: | :---: |
| Die Size | $4.20 * 4.20$ | mm |
| Anode Pad opening | $3.50 * 3.50$ | mm |
| Thickness | $350 \pm 25$ | $\mu \mathrm{~m}$ |
| Anode Metalization (Al) | 4 | $\mu \mathrm{~m}$ |
| Cathode Metalization (Ag) | 0.4 | $\mu \mathrm{~m}$ |
| Frontside Passivation | Polyimide |  |

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## Chip Dimension



| symbol | Dimension $+/-\mathbf{1 0 \%}$ |
| :---: | :---: |
| $A$ | 4.20 mm |
| $B$ | 4.20 mm |
| C | 3.50 mm |
| $D$ | 3.50 mm |
| $H$ | 350 um |

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